

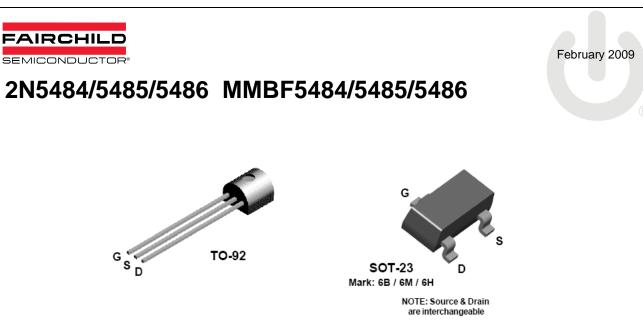
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N-Channel RF Amplifier

This device is designed primarily for electronic switching applications such as low On Resistance analog switching. Sourced from Process 50.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{DG}	Drain-Gate Voltage	25	V
V _{GS}	Gate-Source Voltage	- 25	V
I _{GF}	Forward Gate Current	10	mA
T_{J},T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

<u>NOTES</u>: 1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units
		2N5484-5486	*MMBF5484-5486	
PD	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/°C
R _e Jc	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

© 2007 Fairchild Semiconductor Corporation 2N5484/5485/5486 MMBF5484/5485/5486 Rev. 1.0.0

N-Channel RF Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
	RACTERISTICS					
	Gate-Source Breakdown Voltage		- 25			V
IGSS	Gate Reverse Current	$I_G = -1.0 \ \mu A, V_{DS} = 0$ $V_{GS} = -20 \ V, V_{DS} = 0$	- 25		- 1.0	nA
IGSS	Gate Reverse Current				- 0.2	μΑ
V _{GS(off)}	Gate-Source Cutoff Voltage	$\begin{array}{c} V_{\text{GS}}\text{=-20 V}, V_{\text{DS}}\text{=0}, T_{\text{A}}\text{=100}^{\circ}\text{C} \\ V_{\text{DS}}\text{=15 V}, I_{\text{D}}\text{=10 nA} \textbf{5484} \end{array}$	- 0.3		- 3.0	V
		5485 5486	- 0.5 - 2.0		- 4.0 - 6.0	
		5460	- 2.0		- 0.0	v
ON CHAR	ACTERISTICS					
	Zero-Gate Voltage Drain Current*	V _{DS} = 15 V, V _{GS} = 0 5484	1.0		5.0	mA
033	Zore outo voltage brain ourient	5485	4.0		10	mA
		5486	8.0		20	mA
	GNAL CHARACTERISTICS	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 kHz				
9fs	Forward Transfer Conductance	5484	3000		6000	μmho
		5485	3500		7000	μmho
	land Operaturations	5486	4000		8000	μmho
Re(Yis)	Input Conductance	V _{DS} = 15 V, V _{GS} = 0, f = 100 MHz 5484			100	μmho
		$V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 400 \text{ MHz}$			100	μπιο
		5485 / 5486			1000	μmho
gos	Output Conductance	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 kHz 5484			50	umbo
		5485			60	µmho µmho
		5486			75	μmho
Re ₍ y _{os)}	Output Conductance	V _{DS} = 15 V, V _{GS} = 0, f = 100 MHz			75	
		5484 V _{DS} = 15 V, V _{GS} = 0, f = 400 MHz			75	μmho
		5485 / 5486			100	μmho
Re(Yfs)	Forward Transconductance	V _{DS} = 15 V, V _{GS} = 0, f = 100 MHz				
		5484 V _{DS} = 15 V, V _{GS} = 0, f = 400 MHz	2500			μmho
		5485	3000			μmho
		5486	3500			μmho
Ciss	Input Capacitance	$V_{DS} = 15 V, V_{GS} = 0, f = 1.0 MHz$			5.0	pF
Crss	Reverse Transfer Capacitance	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 MHz			1.0	pF
Coss	Output Capacitance	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 MHz			2.0	pF
NF	Noise Figure	V_{DS} = 15 V, R _G = 1.0 kΩ, f = 100 MHz 5484			3.0	dB
		V _{DS} = 15 V, R _G = 1.0 kΩ, f = 400 MHz 5484		4.0		dB
		V_{DS} = 15 V , R_{G} = 1.0 k Ω ,			2.0	-10
		f = 100 MHz 5485 / 5486			2.0	dB
		V_{DS} = 15 V, R_{G} = 1.0 k Ω ,	1	1	4.0	dB

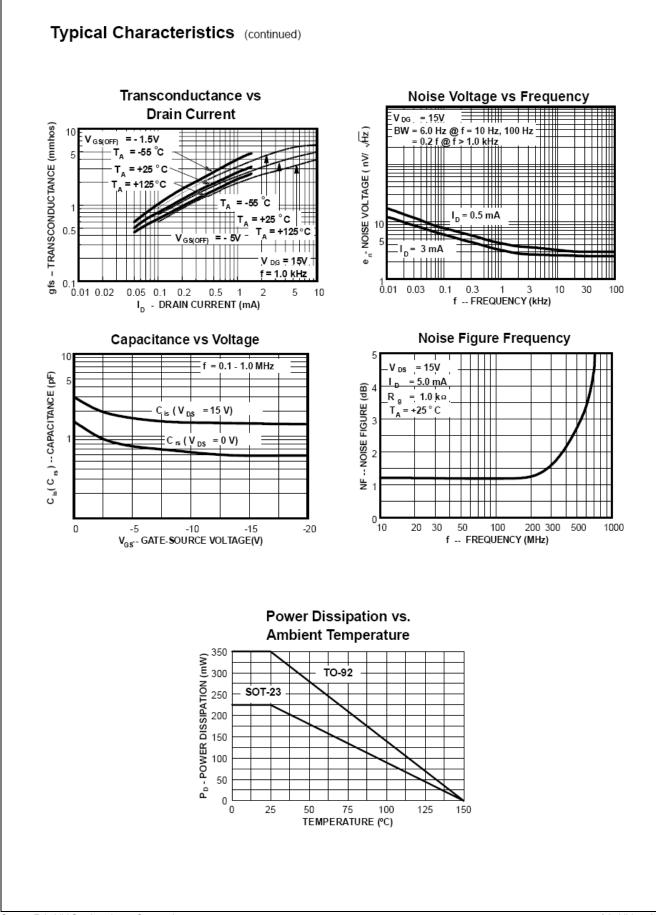
N-Channel RF Amplifier

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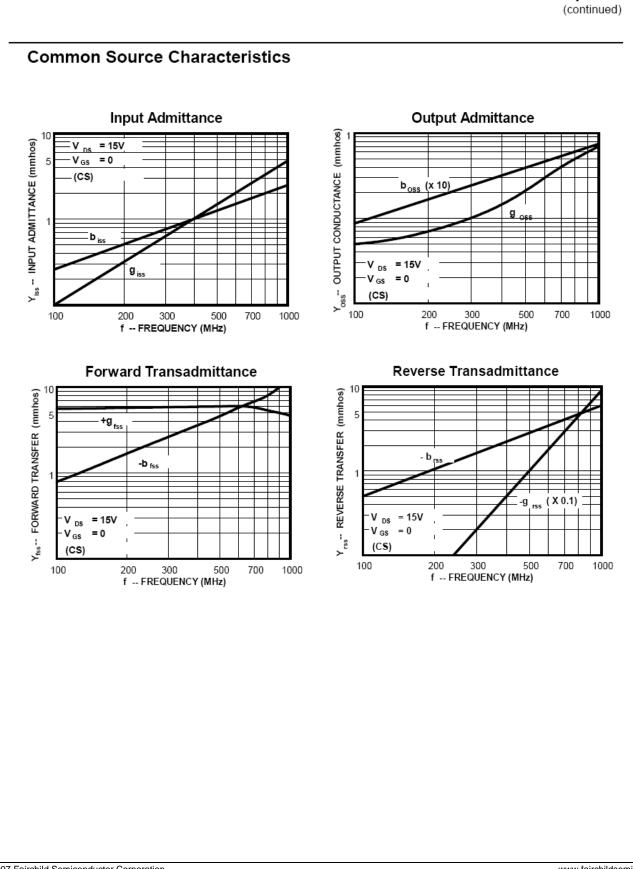
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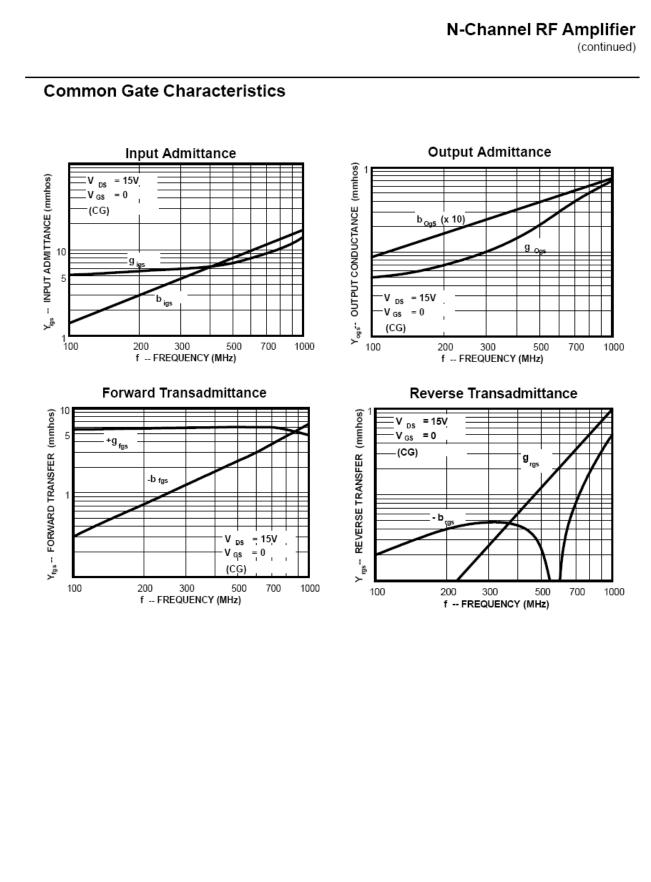
Typical Characteristics Transfer Characteristics **Channel Resistance vs Temperature** 20 1000 -4.5V V GS(OFF) = 15V r_{DS} - DRAIN ON RESISTANCE (Ω) 500 = -55°C T_A -1.0V V_{GS(QFF)} 1(DRAIN CURRENT (mA) 300 = +25 ° C -2.5 V 200 +125° C 12 = -55°C -5.0V TA 100 Τ<u>A</u> = +25 ° C -8.0 V TA +125° C 50 30 ė = 100mV V_{,DS} 20 = 0 V 25 V ν 0 10 0 -2 -4 -5 -50 0 50 100 150 -3 -1 V_{gs}- GATE-SOURCE VOLTAGE(V) TA - AMBIENT TEMPERATURE (C) Common Drain-Source Transconductance Characteristics Characteristics -- TRANSCONDUCTANCE (mmhos) -5 V _{DS} = -55 °C = 15V T_A = +25 ° C I D--- DRAIN CURRENT (mA) = +25 ° C 6 ТҮР v = -5.0V Δ GS(OFF) 2.0V = +125° C 5 0 = -55 °C TA 2 5V 3 = +25 ° C . Т_ 3.0V = +125° C т, 2 3.5V 2 -4.5\ GS(OFF) = 4.0V -2.5 V 0 sf 0 0 0.2 0.4 0.6 0.8 0 1 -3 -1 -2 -4 -5 V_{DS} - DRAIN-SOURCE VOLTAGE(V) V_{gs} GATE-SOURCE VOLTAGE(V) **Output Conductance vs** Transconductance Drain Current Parameter Interactions -- OUTPUT CONDUCTANCE (u mhos) -- DRAIN "ON" RESISTANCE (Ω) 02 gfs, I_{DSS} $P_{SS} @ V_{DS} = 15 V, V_{GS} = 0 PULSE$ $r_{DS} @ V_{DS} = 100mV, V_{GS} = 0$ = +25 °C DRAIN CURRENT (mA) -5.5V 1.0 kHz 5.0\ 20 10V 15V 10 10 5 20\ 20 ν = -3.5V GS(OFF) DSS-- | 0.5 -1.5V @ V_{GS}= 15V, I _D= 1nA V_{GS(OFF)} GS(OFF) ÷ ළී 10 0.1 1 gos . sfg - 2 -3 - 5 0.05 0.1 0.2 0.5 - 7 - 10 1 2 5 10 V GS - GATE-SOURCE VOLTAGE(V) I D-- DRAIN CURRENT (mA)

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N-Channel RF Amplifier







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